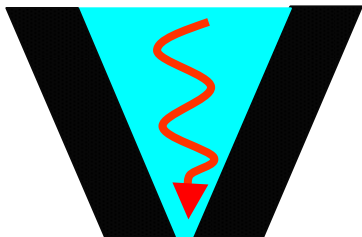


Near-field Optical Microscopy

R. Fernandez, X. Wang, N. Li, K. Parker, and
A. La Rosa

Physics Department

**Portland State University
Portland, Oregon**



Conventional (*Far-Field*) Optical Microscopy

Optical Microscope

Robust and reliable

High throughput

Non-invasive ✓

Low Cost

BUT

Limited Lateral Resolution



Conventional (*Far-Field*) Optical Microscopy

L E N S

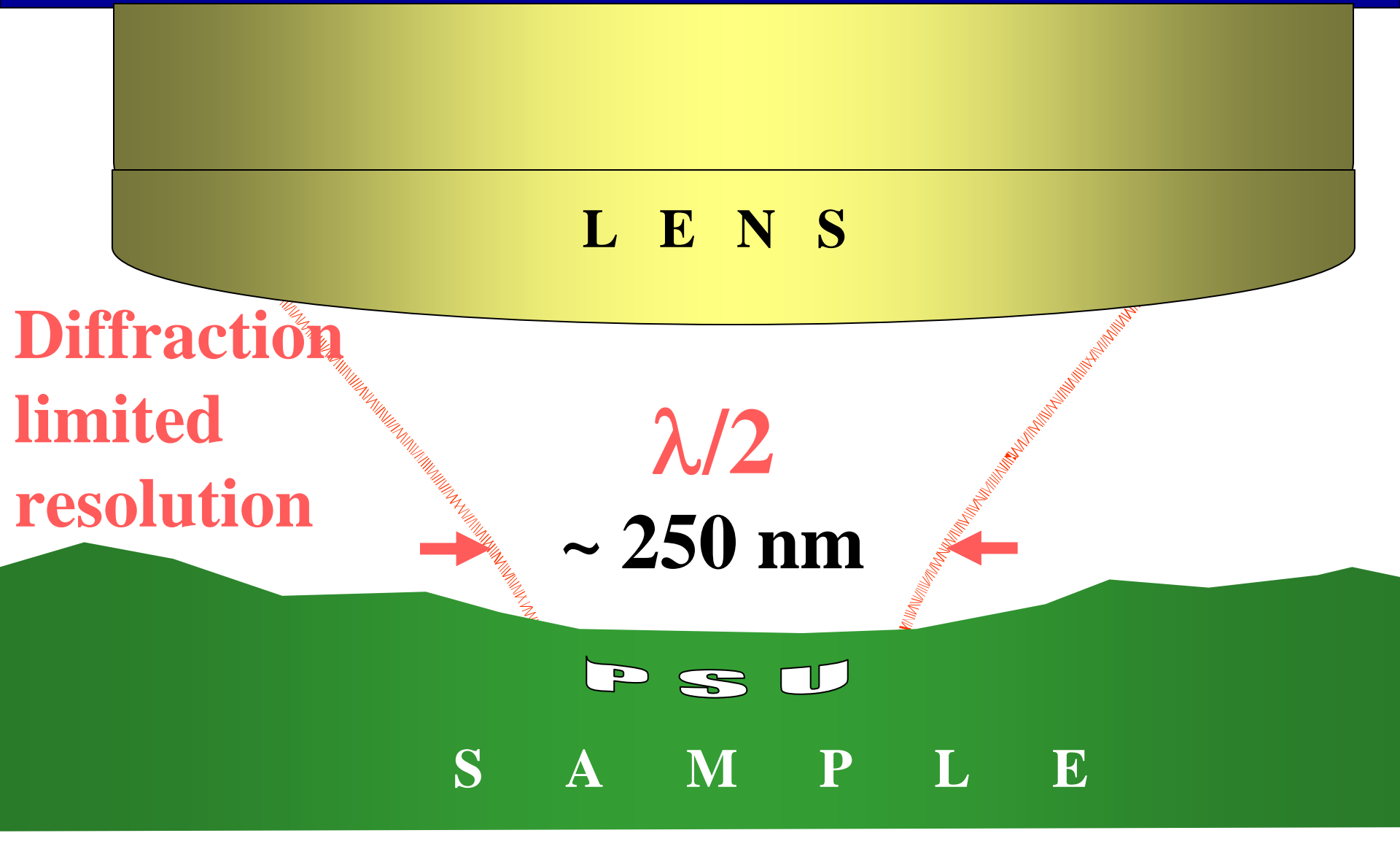
**Diffraction
limited
resolution**

$$\lambda/2$$

~ 250 nm

P S U

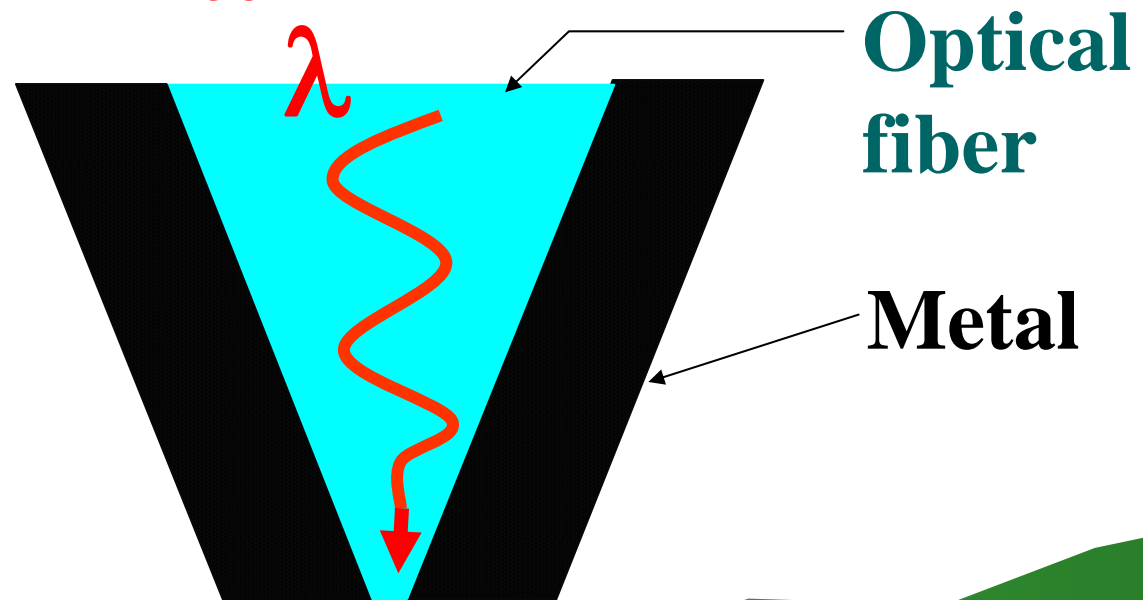
S A M P L E



Near-Field Scanning Optical Microscopy (NSOM)

Surpassing the diffraction limited barrier

PROBE



**Optical
fiber**

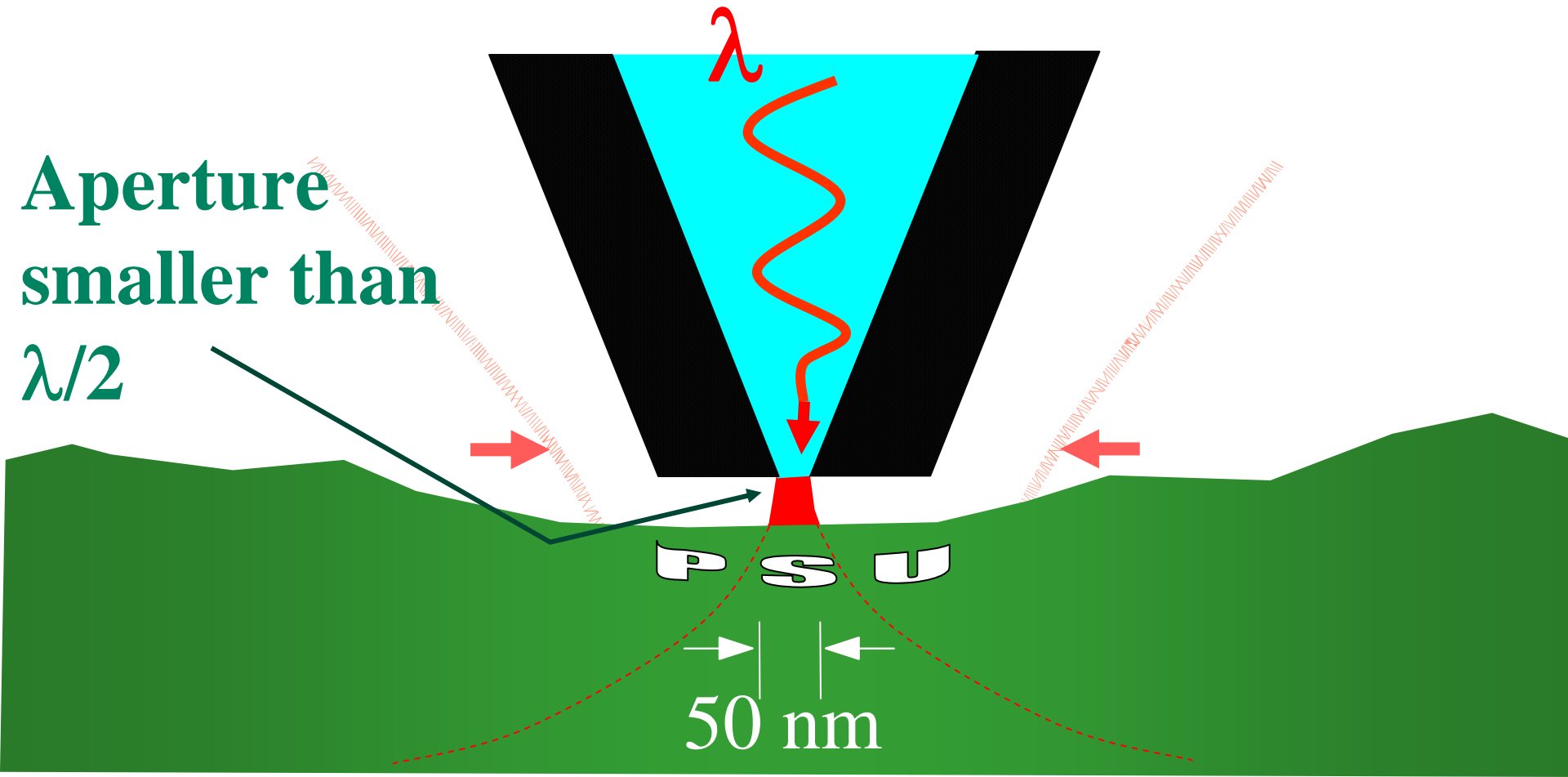
Metal

P S U

50 nm

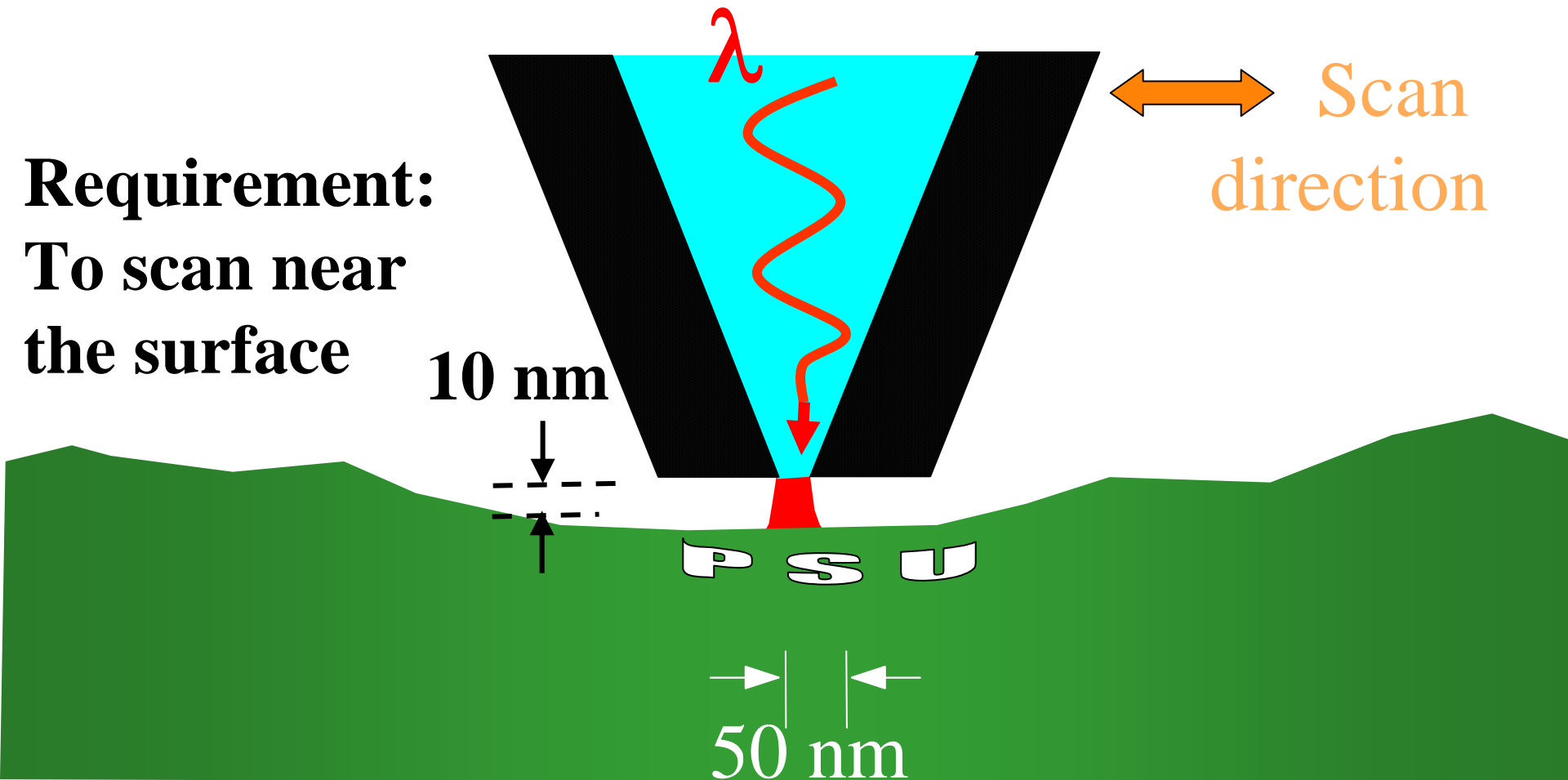
Near-Field Scanning Optical Microscopy (NSOM)

Surpassing the diffraction limited barrier

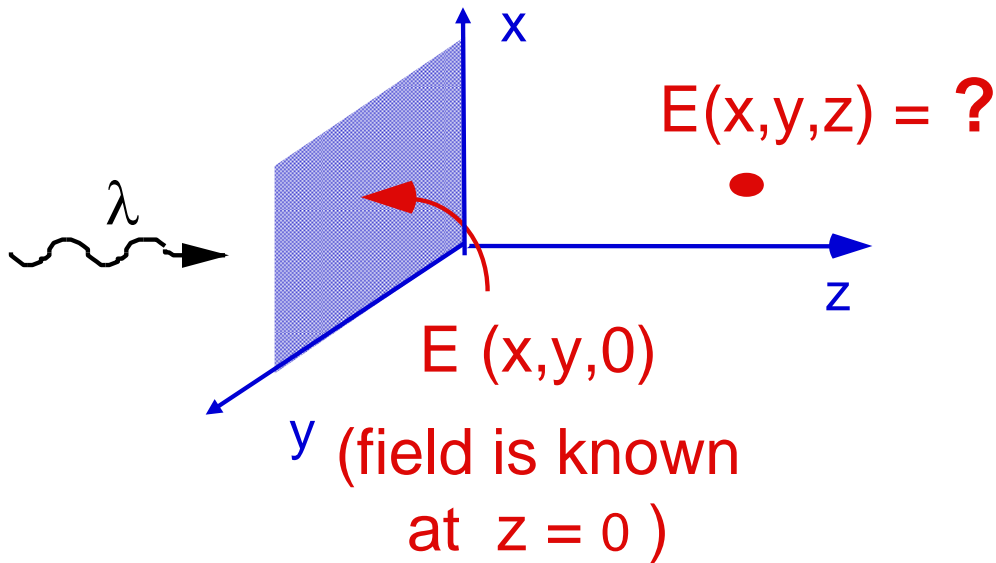


Near-Field Scanning Optical Microscopy (NSOM)

Surpassing the diffraction limited barrier



FOURIER OPTICS



$$\nabla^2 \begin{Bmatrix} \mathbf{E} \\ \mathbf{B} \end{Bmatrix} - \frac{n^2}{c^2} \frac{\partial^2}{\partial t^2} \begin{Bmatrix} \mathbf{E} \\ \mathbf{B} \end{Bmatrix} = \mathbf{0}$$

$$\mathbf{E}(\mathbf{r}, t) = \mathbf{E}(\mathbf{r}) e^{-i\omega t}$$

$$\mathbf{r} = (x, y, z) = (\mathbf{x}, z)$$

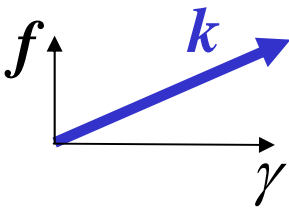
$$E(\mathbf{x}, 0) = \iint [A_f(0)] e^{i2\pi \mathbf{f} \cdot \mathbf{x}} df_x df_y \quad \Longrightarrow \quad E(\mathbf{x}, z) = \iint [A_f(z)] e^{i2\pi \mathbf{f} \cdot \mathbf{x}} df_x df_y ,$$

where $\mathbf{f} = (f_x, f_y)$

$$\nabla^2 E + \left(\frac{2\pi n}{\lambda_0} \right)^2 E = 0 \quad z \geq 0$$

$$\frac{\partial^2}{\partial z^2} [A_f] + (2\pi)^2 \gamma^2 [A_f] = 0, \quad \text{where } \gamma^2 = (n/\lambda)^2 - |\mathbf{f}|^2$$

$e^{i\mathbf{k} \cdot \mathbf{r}}$



$|\mathbf{k}|^2 = (2\pi n / \lambda_0)^2$
 $= \text{const}$

$$E(\mathbf{x}, 0) = \iint_{|\mathbf{f}| < R} [A_f(0) e^{i2\pi \gamma z}] e^{i2\pi \mathbf{f} \cdot \mathbf{x}} df_x df_y$$

Propagating modes

$$+ \iint_{|\mathbf{f}| > R} [A_f(0) e^{-2\pi \gamma' z}] e^{i2\pi \mathbf{f} \cdot \mathbf{x}} df_x df_y$$

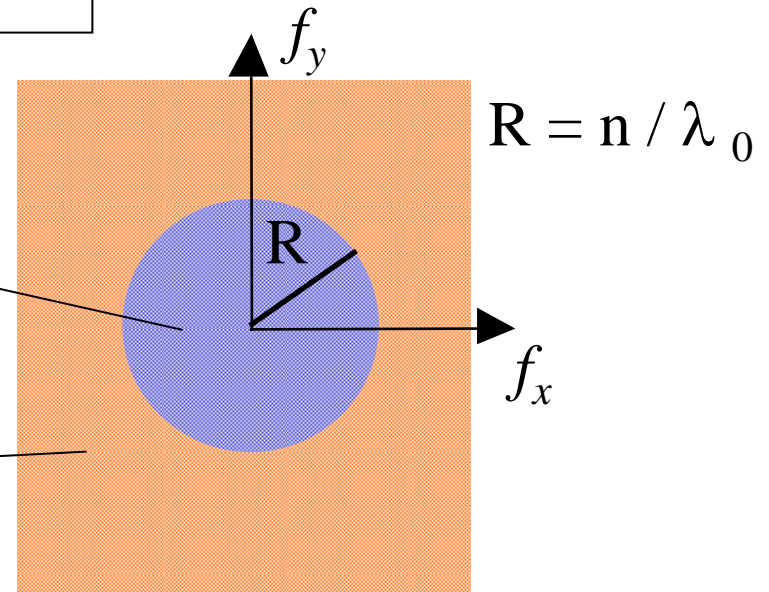
Evanescent modes

Where:

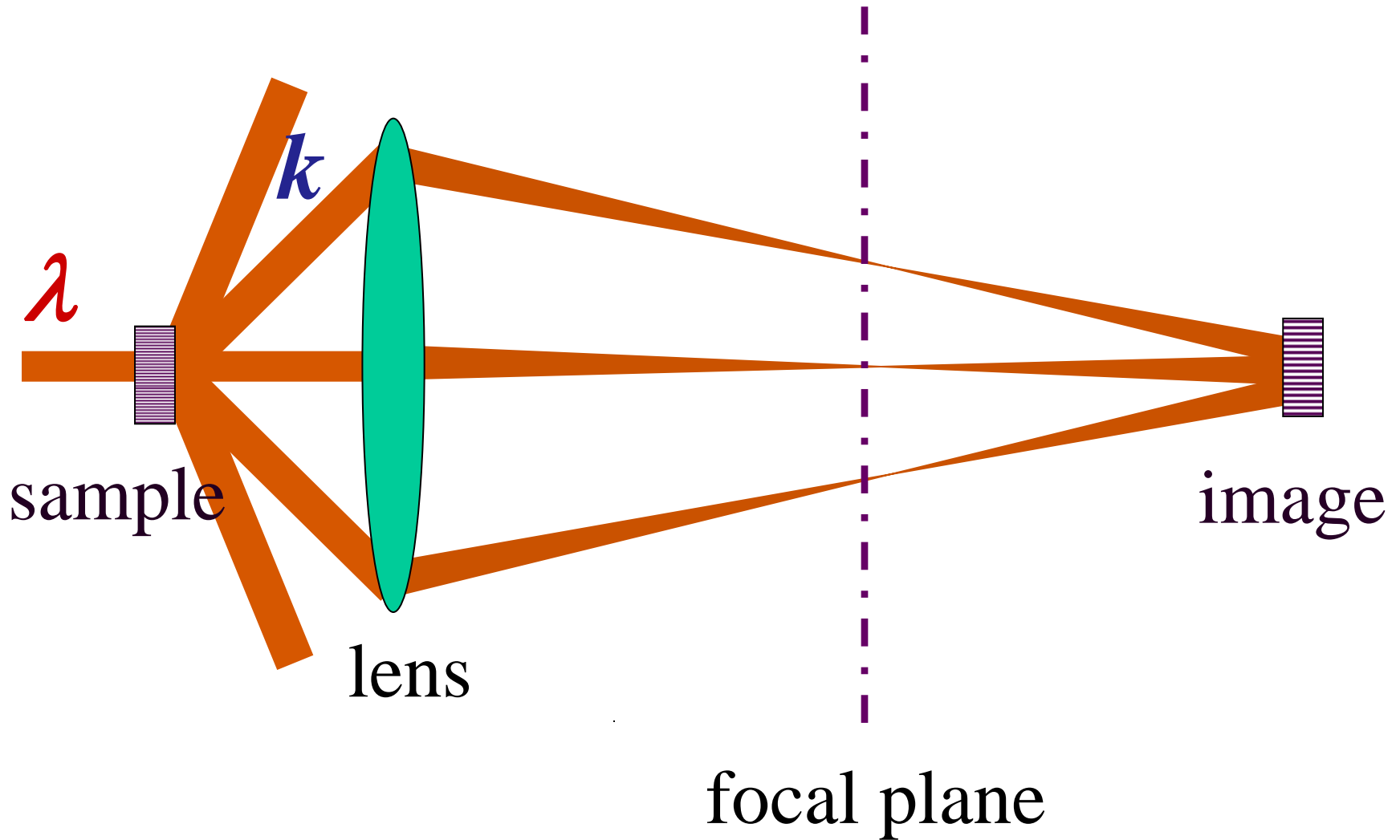
$\gamma^2 = (n / \lambda_0)^2 - |\mathbf{f}|^2$
and
 $\gamma'^2 = |\mathbf{f}|^2 - (n_0 / \lambda)^2$

Propagating modes
region $|\mathbf{f}| < R$

Evanescent modes
region $|\mathbf{f}| > R$



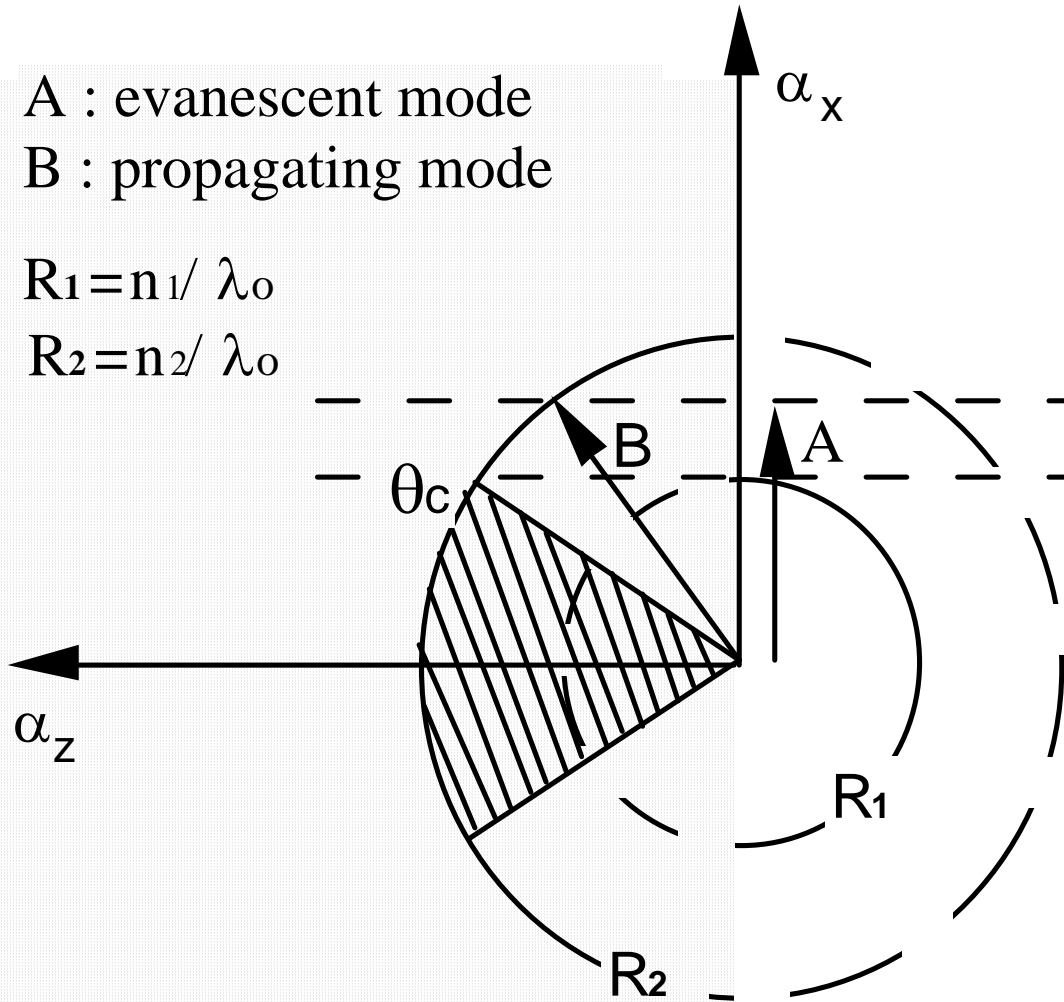
Resolution and Finite Entrance Pupil



A : evanescent mode
B : propagating mode

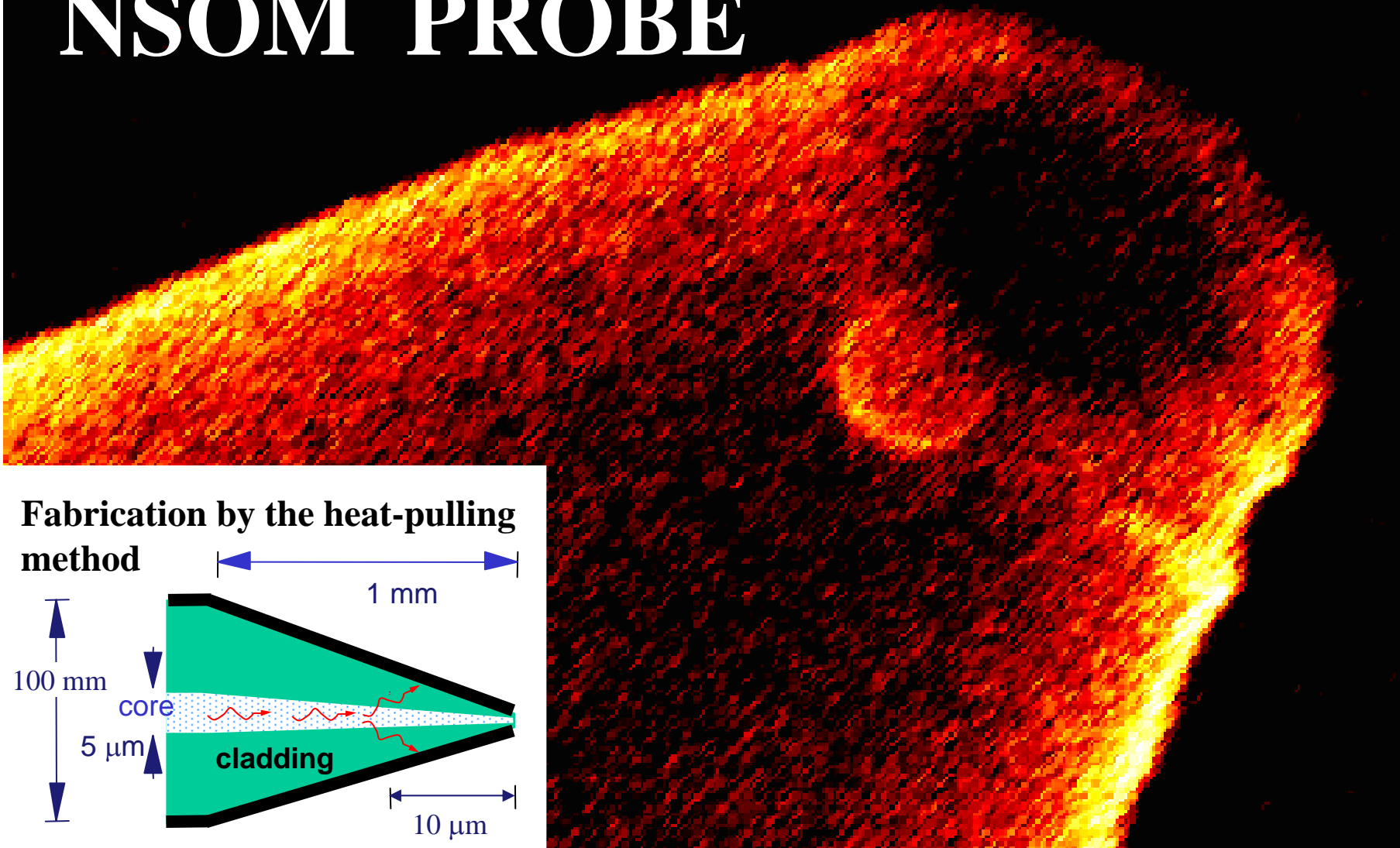
$$R_1 = n_1 / \lambda_0$$

$$R_2 = n_2 / \lambda_0$$

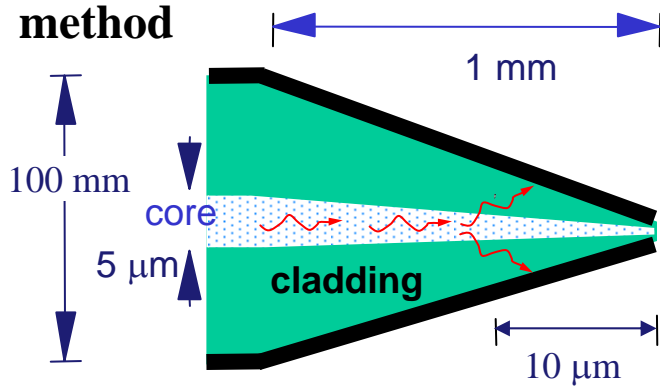


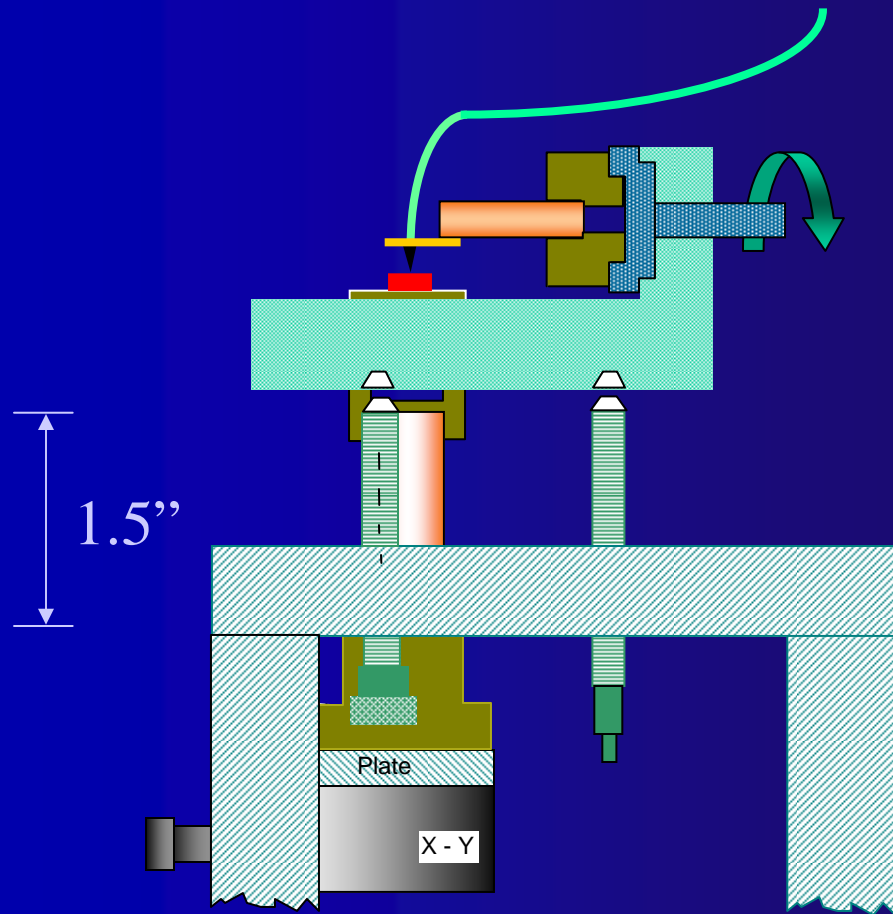
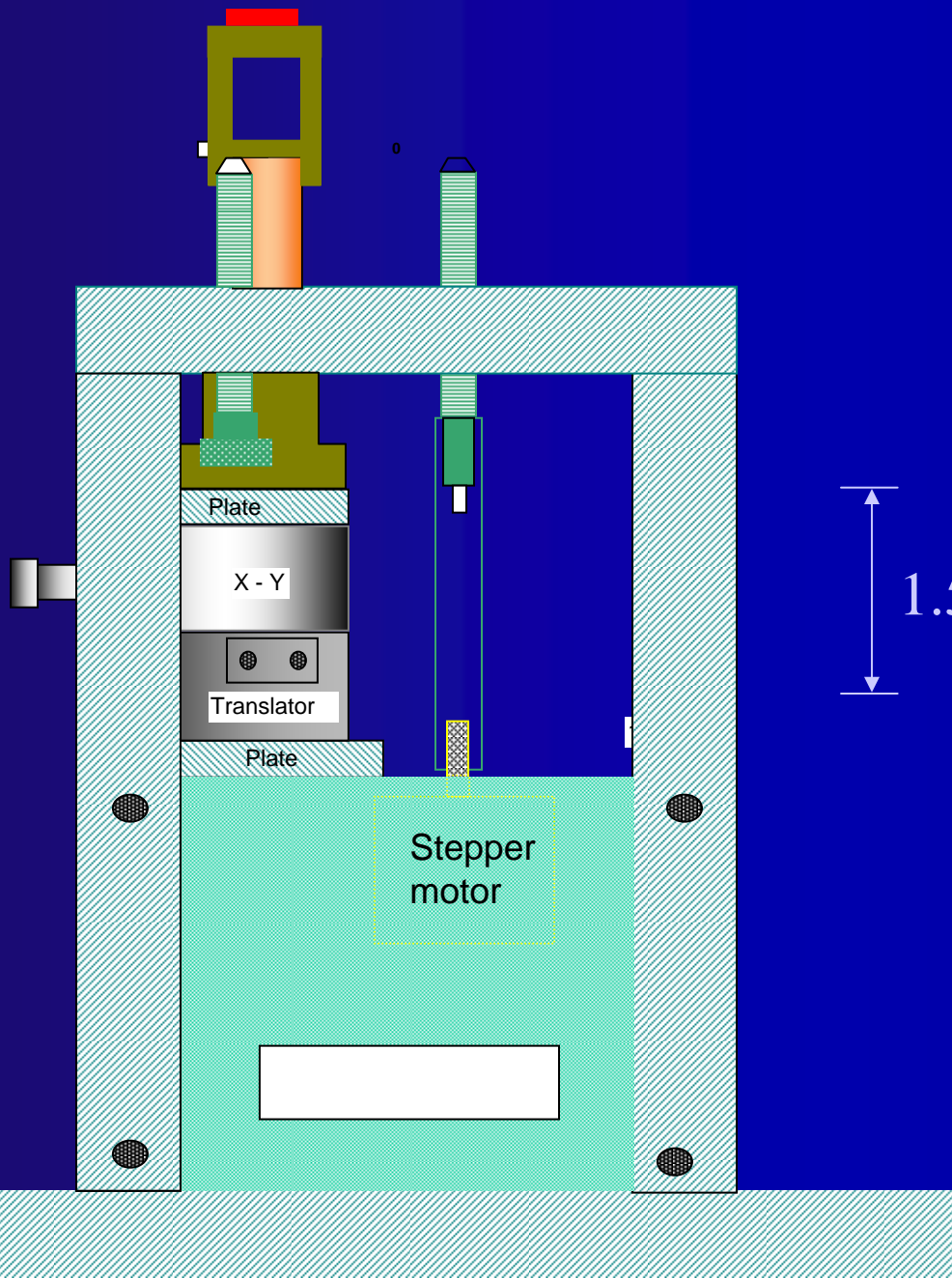
NSOM PROBE

100 nm

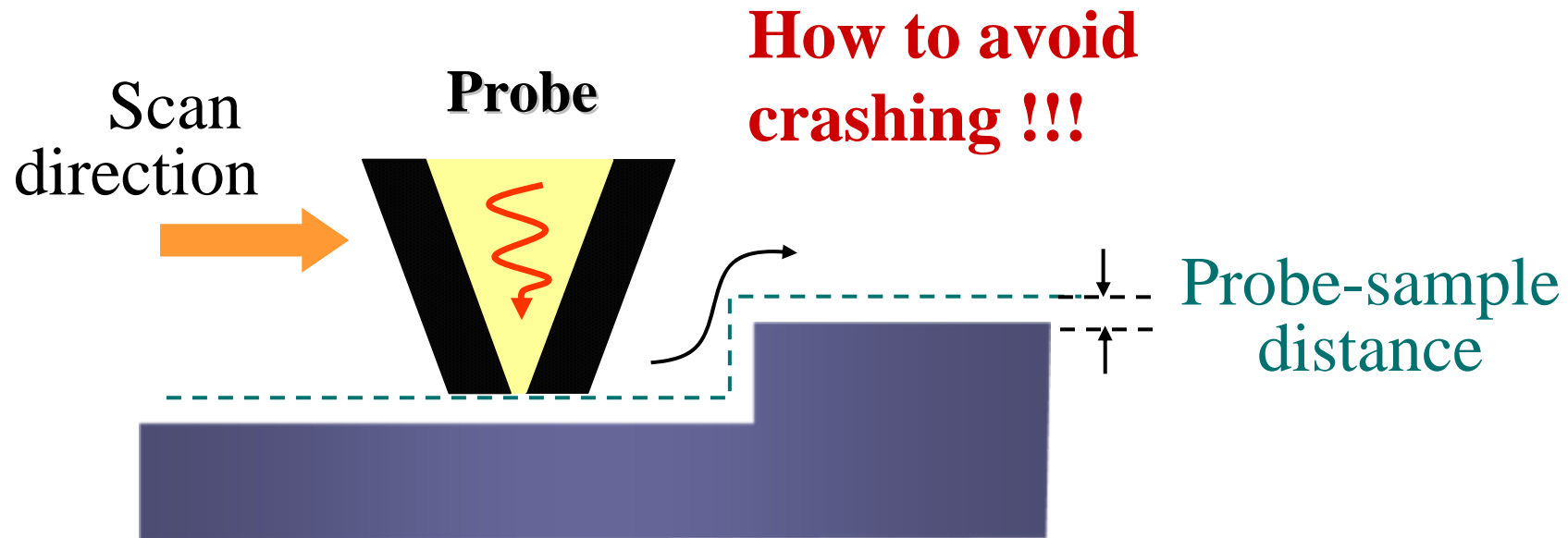


Fabrication by the heat-pulling method





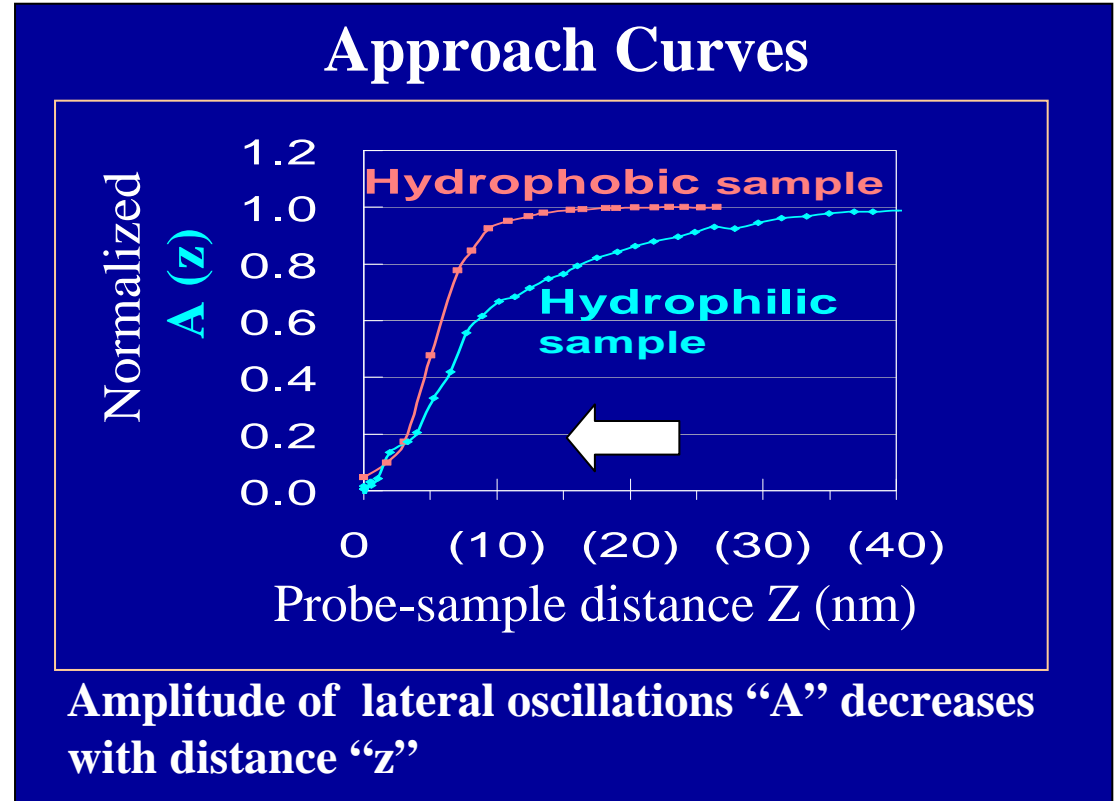
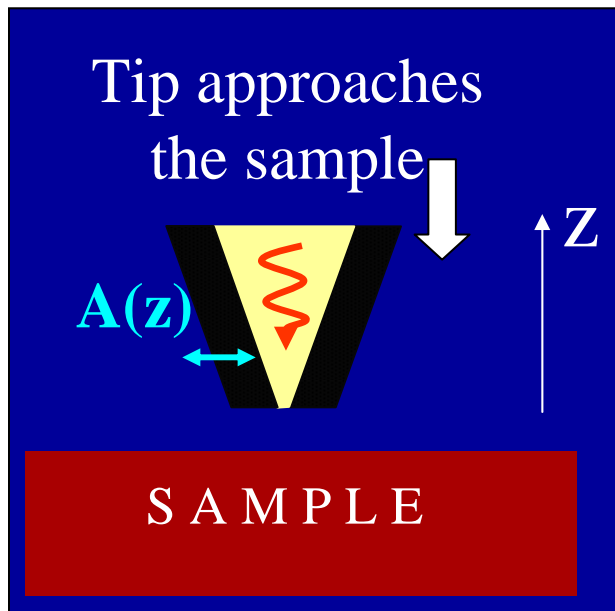
Need of probe-sample distance regulation



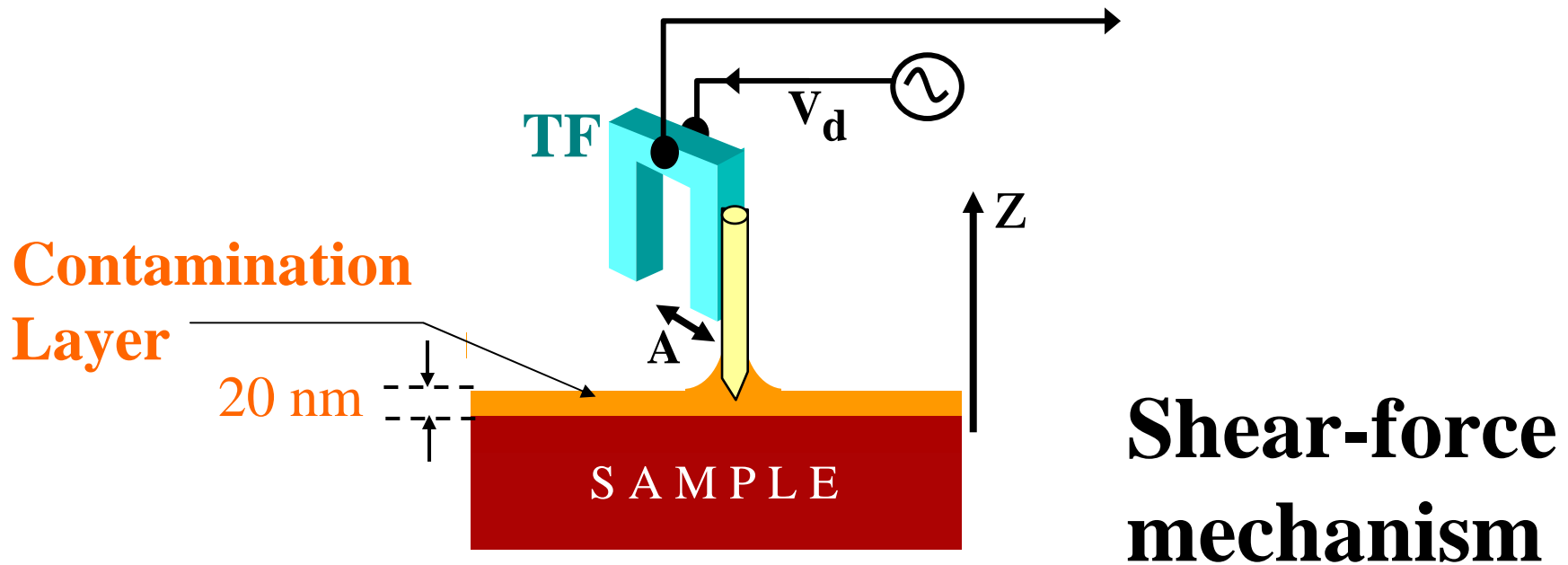
How to automatically control the probe's vertical position?

STRATEGY

- Probe is set to perform lateral oscillation (by an external device.)
- It is observed that the amplitude “A” of the lateral oscillations are damped when the probe’s tip is in the proximity (~ 20 nm) to the sample’s surface.



Damping contamination layer (hypothesis)

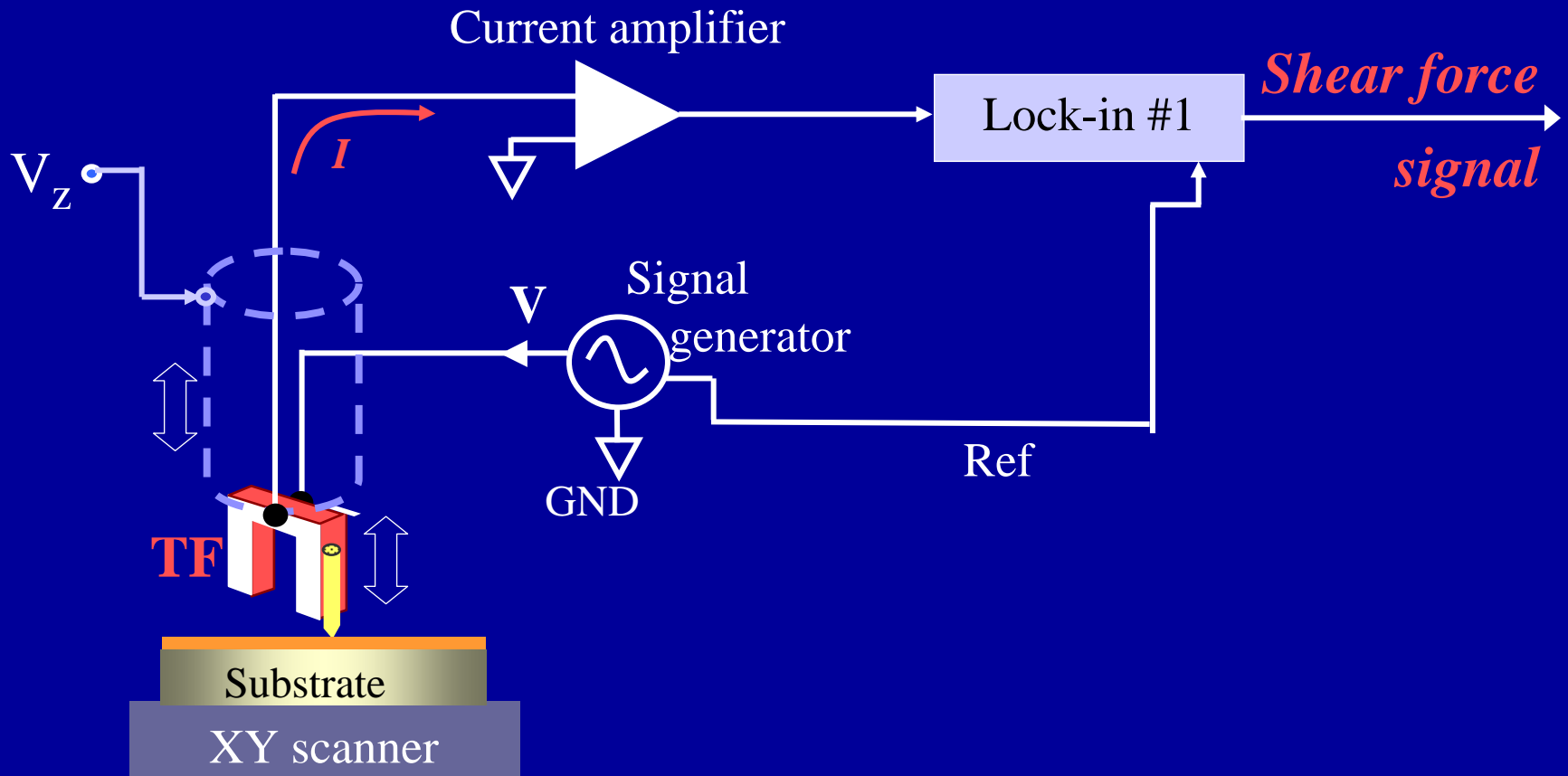


Hypothesis: The damping effect of the contamination layer should produce a distance dependence on the probe's amplitude of oscillations.

$$\text{That is: } A = A(z)$$

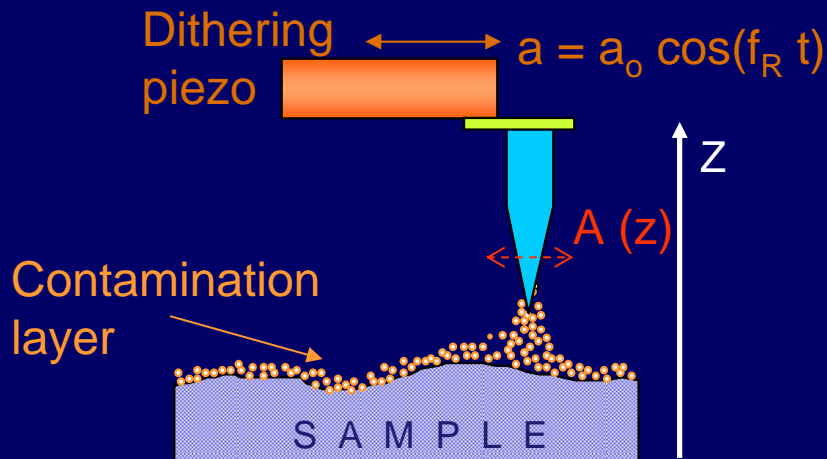
Shear-force detection

Electrical implementation

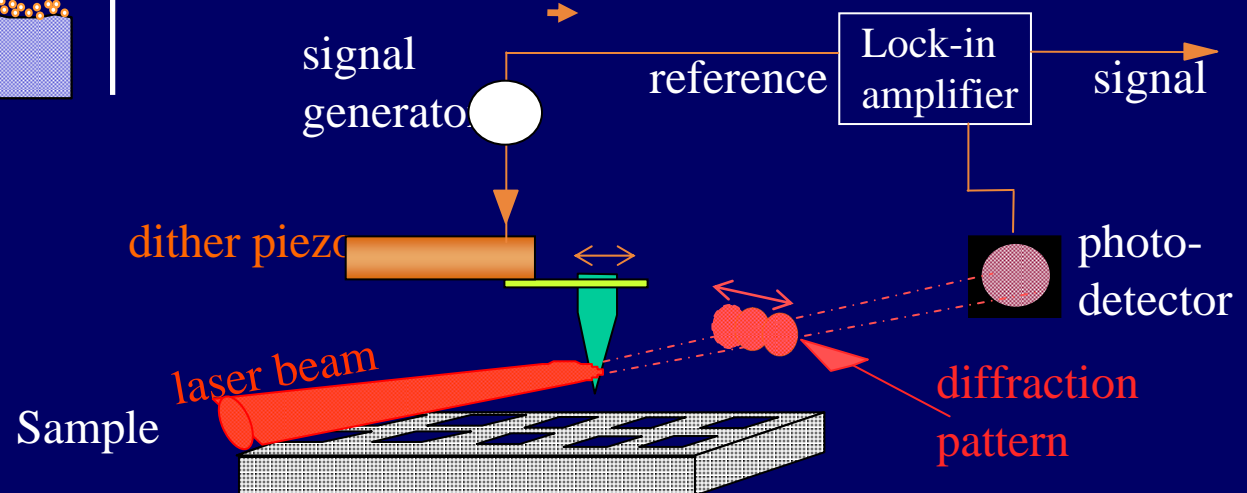
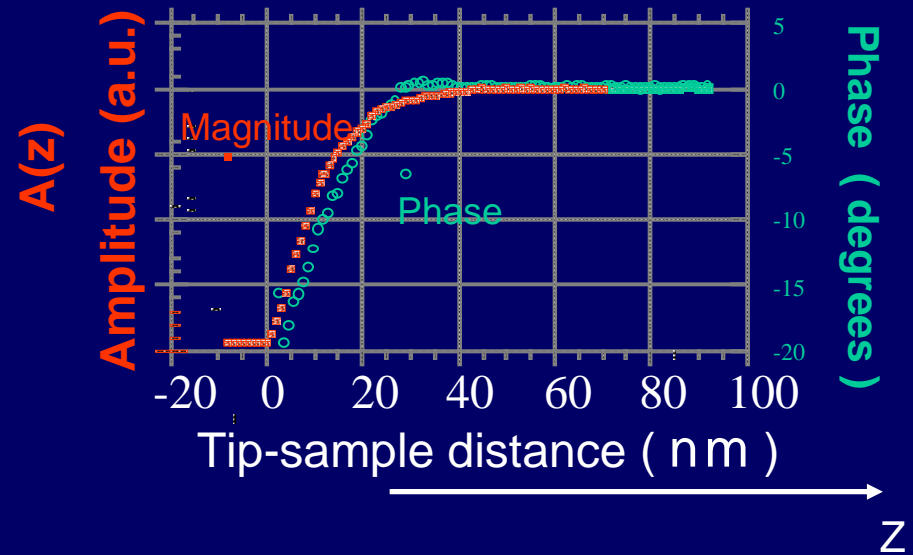


Shear-force detection

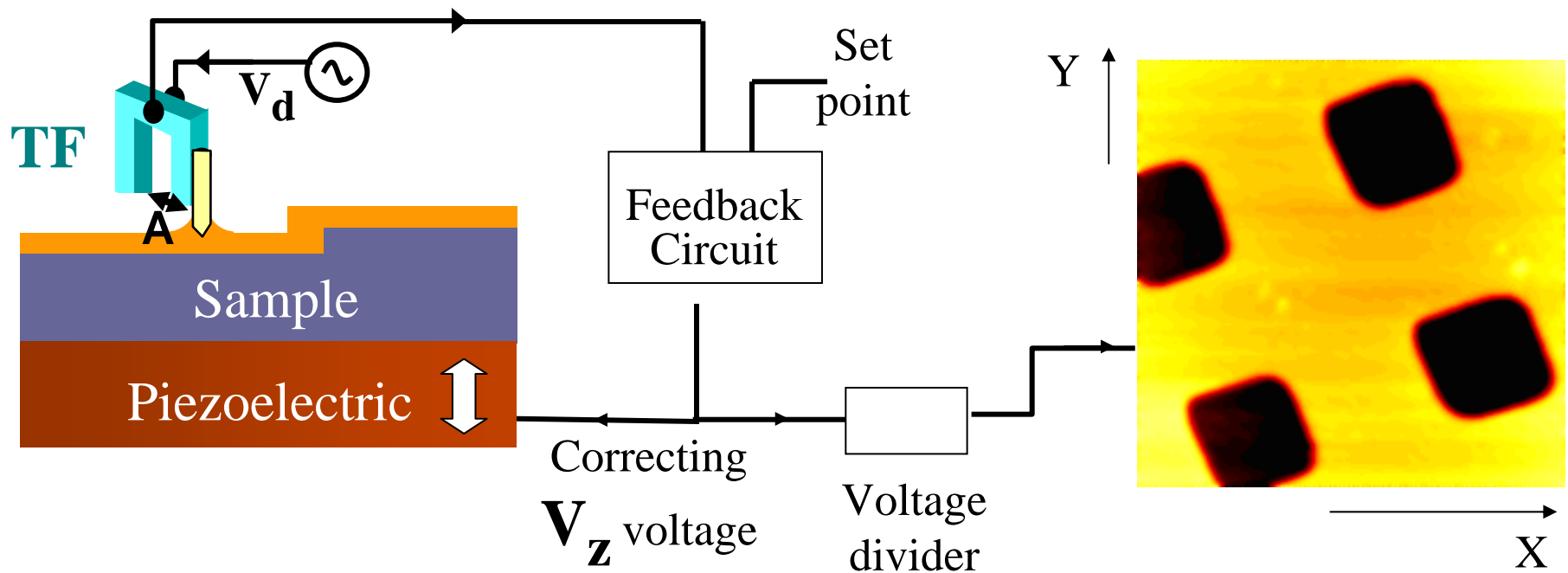
Optical implementation



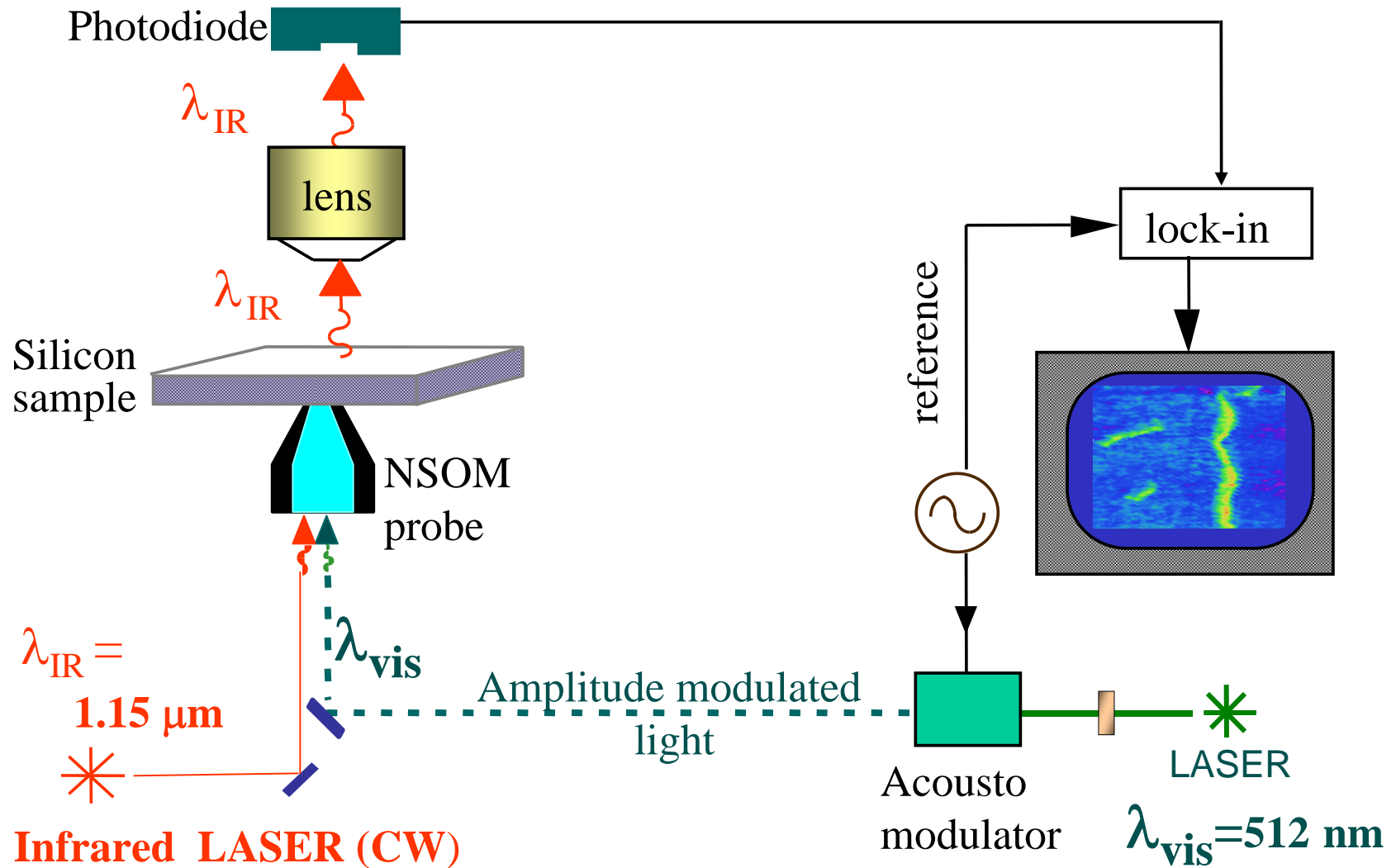
Amplitude of oscillations
 $A = a Q$

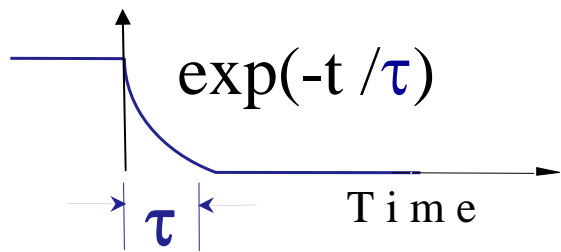


Implementing probe-sample distance regulation in NSOM

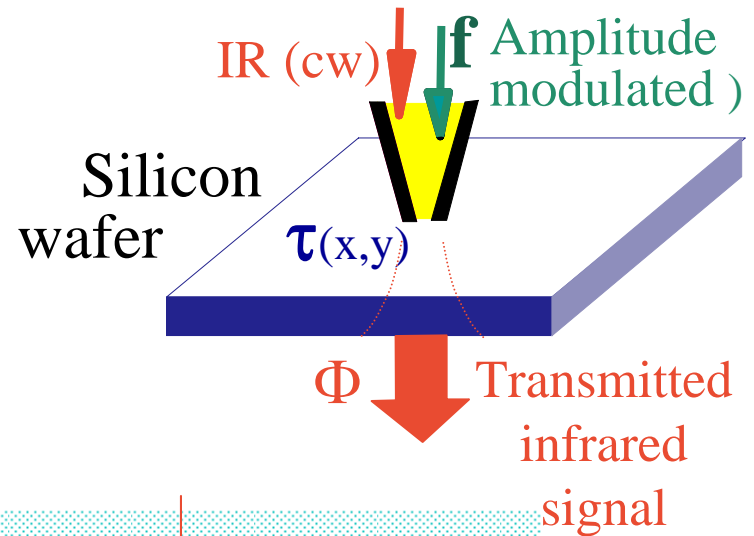


Experimental setup: Freq Resolved Contrast





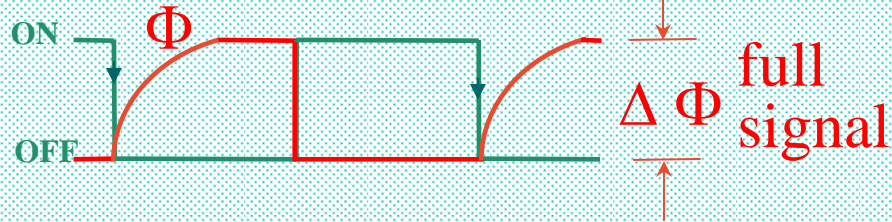
τ : carrier lifetime



Φ AS A FUNCTION OF TIME

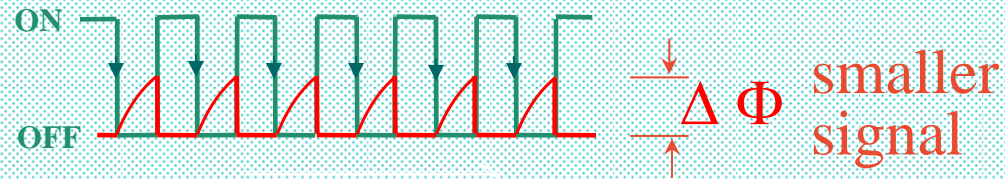
At low frequencies:

$$f < (1 / 2\pi \tau)$$

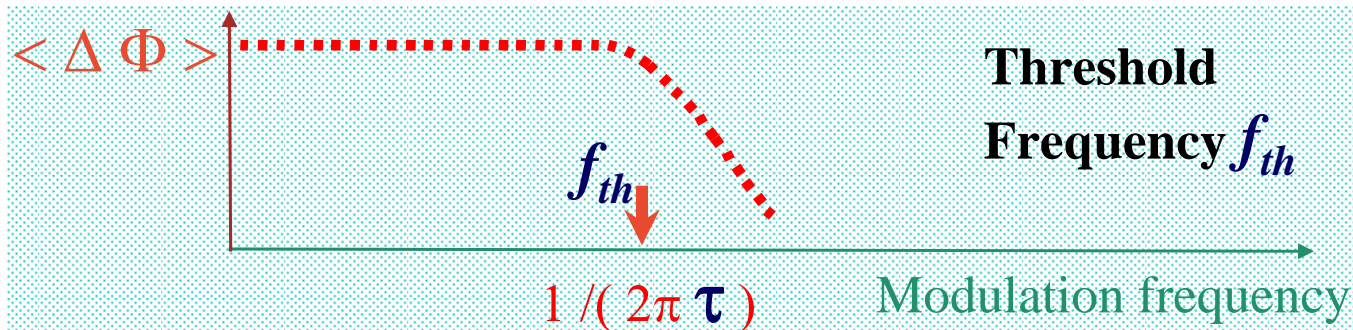


At high frequencies:

$$f > (1 / 2\pi \tau)$$

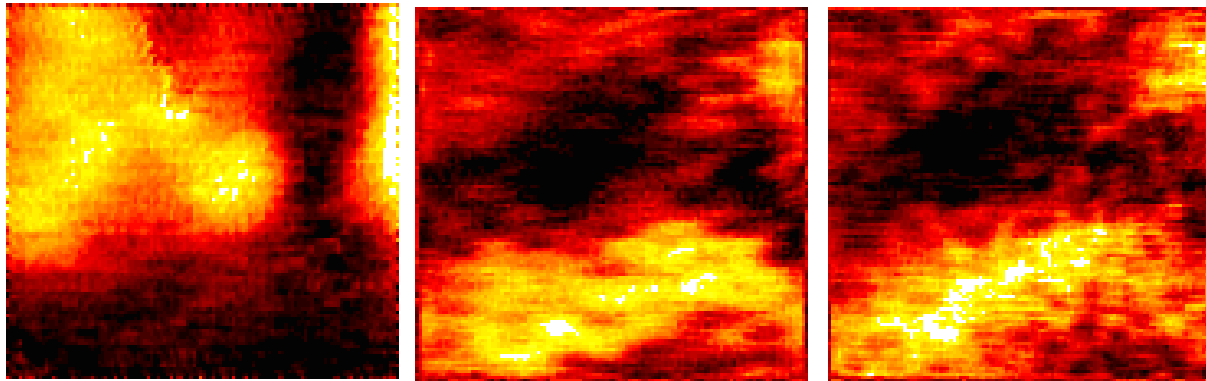


$\langle \Delta \Phi \rangle$ AS A FUNCTION OF FREQUENCY



Frequency Resolved Contrast

Charge Carrier Dynamics in Silicon



100 Hz

1 KHz

20 KHz

Optical excitation frequency

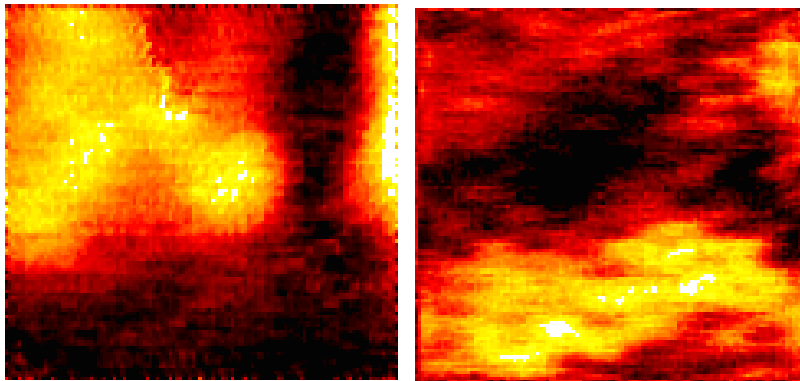
Near-Field images taken over the same region ($7.5 \mu\text{m}^2$)

To be compared with standard (far field) techniques: Resolution $> 1 \text{ mm}$

Carrier Dynamics in Silicon

Near-field measurement

τ -NSOM



100 Hz

1 KHz

Optical excitation frequency

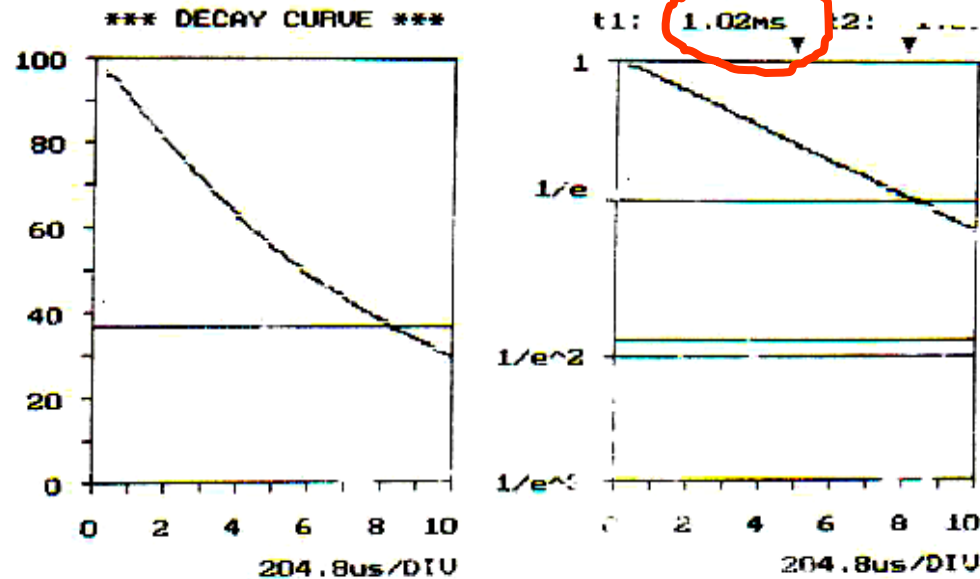
For a threshold frequency of

$f_{th} \sim 100$ Hz:

$$\tau = 1 / (2\pi f_{th}) \sim 1.5 \text{ ms} !$$

Far-field measurement

Laser/Microwave
Lifetech-88, Semitex Co.



	X-POSI (mm)	Y-POSI (mm)	PEAK (mv)	LIFETIME	
				1/e	log
1	+00.0	+30.0	13	1.62 ns	1.65 ns
2					